2D Materials Design for Production of Cold Electrons

Richard G. Hennig, Joshua Paul, Michael Ashton, University of Florida



MPInterfaces - High throughput framework for 2D materials

VASPSol - Ab initio methods for solid/liquid interfaces



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GASP - Genetic algorithm and machine learning for structure predictions

Open source available at <u>https://github.com/henniggroup</u>





Data available at <u>http://materialsweb.org</u>



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Screen 2D materials for photocathodes

- Formation from layered bulk materials
- Semiconductors with small effective masses \bullet
- Promising family of group-IV monochalcogenides



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MPInterfaces - High throughput framework for 2D materials

MPInterfaces

0

sulfur 16

S

32.065

selenium **34**

Se

78.<mark>96</mark>

tellurium 52

Te 127.60

silicon 14

Si

ermanium **32**

Ge

72.64

tin **50**

Sn 118.710

lead **82**

Pb 207.2

phosphor 15

30.974

arsenic **33**

As

74.922

antinomy **51**

Sb 121.76



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5

bSe

SnTe

4.5

Lattice Constant (Å)

[©]PbTe





Acknowledgment

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- VASPsol solvation model and nanocrystals: K. Mathew, J. Gabriel, C. Bealing
- GASP genetic algorithm and machine learning: **B. Revard**, W. Tipton, A. Yesupenko, B. Antonio, S. Honrao • Financial support by NSF-CAREER, NSF-SSI, NIST, DOE-EFRC
- Computational resources provided by HiPerGator@UF and NSF XSEDE



UF ... FLAMES

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2D Materials Beyond Graphene

Materials interfaces

- At the heart of many modern-day critical technologies
- Importance in key industrial segments: Microelectronics, chemical and energy industries

Single-layer or 2D materials

- Maximize their interfacial area
- Properties differ from 3D counterparts
- Potentially many more 2D materials awaiting discovery

Advantages for Photocathodes

- Atomically flat
- Low surface energy, hydrophobic, low reactivity
- Possibly weak interactions with substrates







http://newsroom.intel.com/docs/DOC-2032



Lauritsen et al., J. Catalysis 221 25 (2004)

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Definition: Two-dimensional materials are crystals with structures that are periodic in two dimensions and have finite extension in the third dimension.



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Definition: Two-dimensional materials are crystals with structures that are periodic in two dimensions and have finite extension in the third dimension.

• 2D materials could consist of more than one atomic layer

Structure





BN

GaAs

MoS₂

SnSe





Bi₂Se₃







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Definition: Two-dimensional materials are crystals with structures that are periodic in two dimensions and have finite extension in the third dimension.

- 2D materials could consist of more than one atomic layer
- Electronic, magnetic, etc. properties for electronic and energy applications









Definition: Two-dimensional materials are crystals with structures that are periodic in two dimensions and have finite extension in the third dimension.

- 2D materials could consist of more than one atomic layer
- Substrates for synthesis and chemical properties for processing

Structure





• Electronic, magnetic, etc. properties for electronic and energy applications

Properties

Processing







Materials Informatics of 2D Materials





H. L. Zhuang and RGH, JOM 66, 366 (2014)





Materials Informatics of 2D Materials









Open source available at https://github.com/henniggroup





Information from DFT for photocathodes

• Band structures (gaps, effective masses)



A. K. Singh & RGH Appl. Phys. Lett. 105, 042103 (2014)







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Information from DFT for photocathodes

- Band structures (gaps, effective masses)
- Workfunction and electron affinity







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Information from DFT for photocathodes

- Band structures (gaps, effective masses)
- Workfunction and electron affinity
- Quasiparticle energies (corrections to band structure)

2D SnS₂









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Information from DFT for photocathodes

• Band structures (gaps, effective masses)

2D SnS₂

- Workfunction and electron affinity
- Quasiparticle energies (corrections to band structure)
- Optical transitions and excitons



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Information from DFT for photocathodes

- Band structures (gaps, effective masses)
- Workfunction and electron affinity
- Quasiparticle energies (corrections to band structure)
- Optical transitions and excitons
- Materials stability, Pourbaix diagrams



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Screening of 2D materials:

- 1. Identify layered bulk materials
- 2. Formation energy relative to bulk \Rightarrow 625 stable monolayer
- 3. Monolayers
- 4. Semiconductors
- 5. Semiconductors
- 6. Additional consideration: Dirac-cone 2D materials







- \Rightarrow 826 monolayer candidates
- \Rightarrow 282 semiconductors (0 < $E_{gap} \leq 3eV$)
- \Rightarrow 81 with direct gap
- \Rightarrow 201 with indirect gap
- \Rightarrow 21 with $m_{\text{effective}} < 1 m_{\text{e}}$

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- Many layered structures exist in materials that can be used to synthesize monolayers Identifying layered compounds using data from <u>MaterialsProject.org</u> using bond topology
- a) $Ta_{2}Te_{3}$ (mp-542634)











- d) Li-WCl₆ (mp-570512) c) $Ge_{2}Te_{5}As_{2}(mp-14791)$
- M. Ashton, J. Paul, S. Sinnott, RGH submitted (2016)





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van der Waals	2D Materials	File:Pyrene 3D	Publications »	Materials Project	Material mp-27
~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~		Ho	me About <del>-</del> .	Apps - Docum	entation <del>-</del> API
MATERIAL	ID:				
SiP	mp-2798				
HM:P 1 a=3.531Å b=20.567Å c=15.611Å α=90.000° β=90.000° γ=90.000°				Material Deta Final Magnetic -0.000 µB Magnetic Order Unknown Formation Ener -0.156 eV Energy Above F	ails Moment ring rgy / Atom Hull / Atom
	会交	台文		Density 2.08 g/cm ³	
	B P	BR		Decomposes To Stable	0
Structure Type:	Conventional Standard	Primitive Refined		Band Gap 1.740 eV	
Space Filling	Polyhedr	a		Space Group	)



M. Ashton, J. Paul, S. Sinnott, RGH submitted (2016)

• Search MaterialsProject Database for layered 3D structures with van der Waals gap







### Search MaterialsProject Database for layered 3D structures with van der Waals gap



### Identified 826 unique layered 3D bulk candidate materials for exfoliation.



M. Ashton, J. Paul, S. Sinnott, RGH submitted (2016)







### • Search MaterialsProject Database for layered 3D structures with van der Waals gap



### Identified 826 unique layered 3D bulk candidate materials for exfoliation.

### Identified 625 2D materials with energy below 150 meV/atom



M. Ashton, J. Paul, S. Sinnott, RGH submitted (2016)





## **Electronic Properties of 2D Materials**

- Identify 2D materials with PBE bandgap between 0 and 3 eV
- Among the 625 stable monolayers, 282 are semiconductors (about 46%)
  - > 201 materials with indirect gap
  - 81 materials with direct gap









## **Effective Electron Masses of 2D Materials**





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Preliminary results for effective masses obtained with PBE functional





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Preliminary results for effective masses obtained with PBE functional

Band gap (eV)





## **Exotic Electronic Properties of 2D Materials**

### **2D** materials with zero gap

- Graphene
- TiNI
- Nb3IrS8
- HfSiTe
- ZrBr
- InBi
- SrSbSe2F
- NiP2
- YIC
- ZrGeTe
- YBrC
- ZrTe5
- HfTe5









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## Website: <a href="https://materialsweb.org">https://materialsweb.org</a>



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### **MPInterfaces**

### High throughput framework for 2D materials



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